Diode Semiconductor Device - Page 1 of 1

AeroBase Group

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	nting Facility Quantity:
1	
	nting Method:
	aded stud
	ady Qty Per Inch (tpi):
32	
	ad Size:
0.138	Binches
Semi	conductor Material:
Silico	n
Volta	ge Rating In Volts Per Characteristic:
100.0	) regulator voltage, dc
Curre	ent Rating Per Characteristic:
10.00	) microamperes forward current, average peak
Powe	er Rating Per Characteristic:
10.0	watts small-signal input power, common-collector preset
Maxi	mum Operating Tempurature Per Measurement Point:
175.0	) degrees celsius case
Threa	ad Series Designator:
Unc	
Term	inal Type And Quantity:
2 ribb	bon
Shelf	Life:
N/a	
Unit	Of Measure:
Demi	litarization:
Yes -	demil/mli
Fiig:	
A110	a0